Small Signal MOSFET

-20 V, -180 mA, Dual P-Channel, 1.0 x 1.0 mm SOT-963 Package

Features

- Dual P-Channel MOSFET
- Offers a Low $R_{DS(ON)}$ Solution in the Ultra Small 1.0 x 1.0 mm Package
- 1.5V Gate Voltage Rating
- Ultra Thin Profile (< 0.5 mm) Allows It to Fit Easily into Extremely Thin Environments such as Portable Electronics.
- These are Pb-Free Devices

Applications

- General Purpose Interfacing Switch
- Optimized for Power Management in Ultra Portable Equipment

MAXIMUM RATINGS (T_{.1} = 25°C unless otherwise specified)

Para	Symbol	Value	Unit			
Drain-to-Source Voltage	V _{DSS}	-20	V			
Gate-to-Source Voltag	е		V _{GS}	±8	V	
Continuous Drain	$T_A = 25^{\circ}C$		-140			
Current (Note 1)	State	$T_A = 85^{\circ}C$	I_{D}	-100	mA	
	t ≤ 5 s			-180		
Power Dissipation			-125			
(Note 1)	(Note 1) State $T_A = 25^{\circ}C$				mW	
			-200			
Pulsed Drain Current		t _p = 10 μs	I _{DM}	-600	mA	
Operating Junction and	T _J , T _{STG}	-55 to 150	°C			
Source Current (Body D	I _S	-200	mA			
Lead Temperature for S (1/8" from case for 1	TL	260	°C			

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

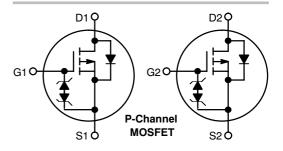
- Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.
- 2. Pulse Test: pulse width \leq 300 μ s, duty cycle \leq 2%

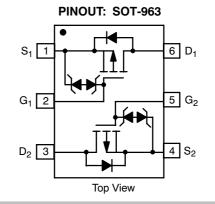


ON Semiconductor®

http://onsemi.com

V _{(BR)DSS} R _{DS(ON)} MAX		I _D Max	
-20 V	5.0 Ω @ -4.5 V		
	7.0 Ω @ -2.5 V	-0.18 A	
	10 Ω @ -1.8 V	-0.16 A	
	14 Ω @ -1.5 V		









MARKING

R = Specific Device Code

M = Date CodePb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 3)	R_{\thetaJA}	1000	°C/W
Junction-to-Ambient – t = 5 s (Note 3)		600	

^{3.} Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS	•						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$		-20			V
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 \text{ V}, V_{DS} = -5.0 \text{ V}$	T _J = 25°C			-50	
			T _J = 85°C			-200	nA
		V _{GS} = 0 V, V _{DS} = -16 V	T _J = 25°C			-100	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} =	±5.0 V			±100	nA
ON CHARACTERISTICS (Note 4)	_						
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_D = -2$	250 μΑ	-0.4		-1.0	V
Drain-to-Source On Resistance	R _{DS(ON)}	$V_{GS} = -4.5 \text{ V}, I_D =$	-100 mA		4.0	5.0	
		V _{GS} = -2.5 V, I _D =	-50 mA		5.0	7.0	
		V_{GS} = -1.8 V, I_{D} = -20 mA V_{GS} = -1.5 V, I_{D} = -10 mA V_{GS} = -1.2 V, I_{D} = -1.0 mA			6.5	10	Ω
					7.5	14	
					11.5		
Forward Transconductance	9FS	V _{DS} = -5.0 V, I _D = -125 mA			0.26		S
Source-Drain Diode Voltage	V _{SD}	$V_{GS} = 0 \text{ V}, I_D = -10 \text{ mA}$			-0.65	-1.0	V
CHARGES, CAPACITANCES AND GATE	RESISTANCE						
Input Capacitance	C _{ISS}				12		
Output Capacitance	Coss	f = 1 MHz, V _{GS} = 0 V V _{DS} = -15 V			2.7		pF
Reverse Transfer Capacitance	C _{RSS}	100 - 101			1.0		
SWITCHING CHARACTERISTICS, V _{GS} = 4.5 V (Note 4)							
Turn-On Delay Time	t _{d(ON)}	V _{GS} = -4.5 V, V _{DD} = -15 V,			20		
Rise Time	t _r				37		
Turn-Off Delay Time	t _{d(OFF)}	$I_D = -180 \text{ mA}, R_G = 2.0 \Omega$			112		ns
Fall Time	t _f				97		1

^{4.} Switching characteristics are independent of operating junction temperatures

TYPICAL PERFORMANCE CURVES

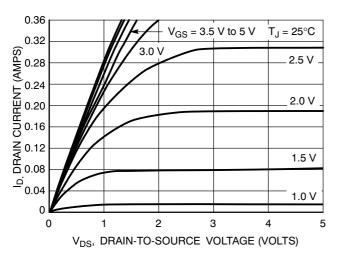


Figure 1. On-Region Characteristics

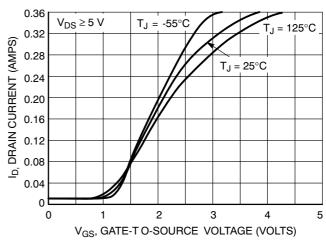


Figure 2. Transfer Characteristics

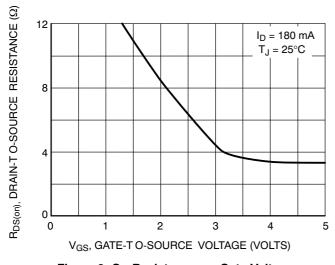


Figure 3. On-Resistance vs. Gate Voltage

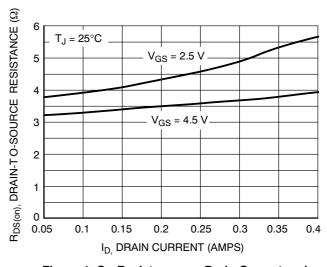


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

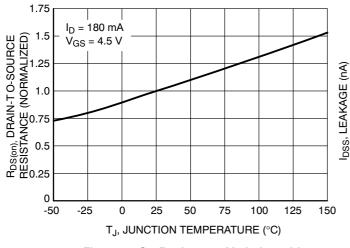


Figure 5. On-Resistance Variation with Temperature

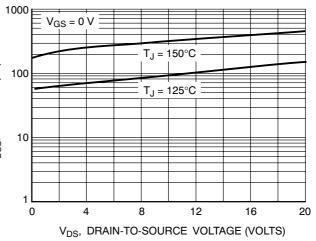


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES

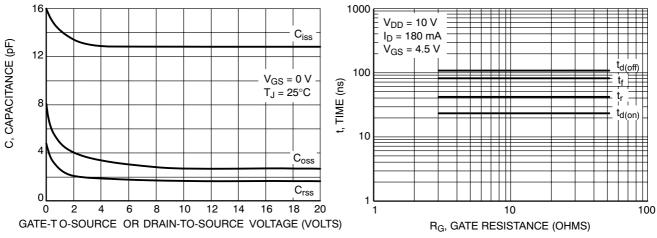


Figure 7. Capacitance Variation

Figure 8. Resistive Switching Time Variation vs. Gate Resistance

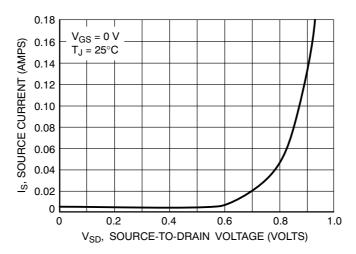


Figure 9. Diode Forward Voltage vs. Current

ORDERING INFORMATION

Device	Package	Shipping [†]
NTUD3129PT5G	SOT-963 (Pb-Free)	8000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

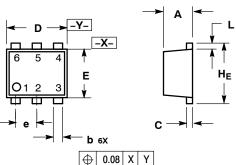
STYLE 10:

PIN 1. CATHODE 1 2. N/C 3. CATHODE 2 4. ANODE 2 5. N/C 6. ANODE 1



SOT-963 CASE 527AA-01 ISSUE D

DATE 30 JUL 2008



	b ex	C → ←
STYLE 1:	STYLE 2:	STYLE 3:

PIN 1. EMITTER 1 2. BASE 1 3. COLLECTOR 2 4 FMITTER 2	PIN 1. EMITTER 1 2. EMITTER2 3. BASE 2 4. COLLECTOR 2	PIN 1. CATHODE 1 2. CATHODE 1 3. ANODE/ANODE 2 4. CATHODE 2 5. CATHODE 2 6. ANODE/ANODE 1
STYLE 4: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	STYLE 5: PIN 1. CATHODE 2. CATHODE 3. ANODE 4. ANODE 5. CATHODE 6. CATHODE	STYLE 6: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
PIN 1. CATHODE 2. ANODE 3. CATHODE	STYLE 8: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.40	0.45	0.50	0.016	0.018	0.020
b	0.10	0.15	0.20	0.004	0.006	0.008
С	0.05	0.10	0.15	0.002	0.004	0.006
D	0.95	1.00	1.05	0.037	0.039	0.041
Е	0.75	0.80	0.85	0.03	0.032	0.034
е	0.35 BSC			(0.014 BS	C
L	0.05	0.10	0.15	0.002	0.004	0.006
HΕ	0.95	1.00	1.05	0.037	0.039	0.041

GENERIC MARKING DIAGRAM*

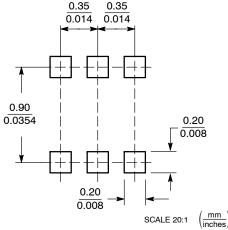


= Specific Device Code Χ

= Month Code Μ

*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " ■", may or may not be present.
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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